

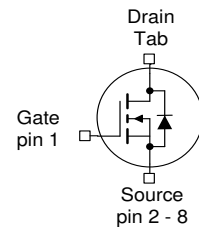
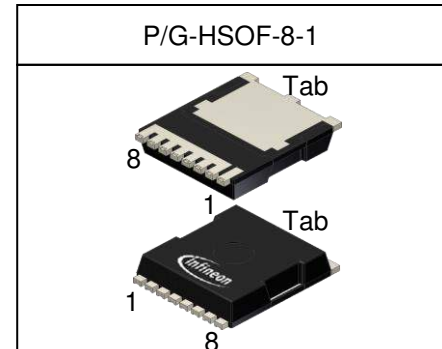
**OptiMOS™-5 Power-Transistor**

**Features**

- N-channel - Enhancement mode
- AEC-Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- Ultra low Rds(on)
- 100% Avalanche tested

**Product Summary**

$V_{DS}$	100	V
$R_{DS(on)}$	1.9	mΩ
$I_D$	260	A



Type	Package	Marking
IAUT260N10S5N019	P/G-HSOF-8-1	5N10019

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}, V_{GS}=10\text{V}$	260	A
		$T_C=100\text{ °C}, V_{GS}=10\text{ V}^{1)}$	197	
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	1040	
Avalanche energy, single pulse <sup>1)</sup>	$E_{AS}$	$I_D=130\text{ A}$	400	mJ
Avalanche current, single pulse	$I_{AS}$	-	220	A
Gate source voltage	$V_{GS}$	-	±20	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	300	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	-	-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics<sup>1)</sup></b>						
Thermal resistance, junction - case	$R_{thJC}$	-	-	-	0.5	K/W

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=210\text{ }\mu\text{A}$	2.2	3.0	3.8	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=50\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=85\text{ }^\circ\text{C}^{1)}$	-	1	20	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=6\text{ V}$ , $I_D=65\text{ A}$	-	2.0	2.5	m $\Omega$
		$V_{GS}=10\text{ V}$ , $I_D=100\text{ A}$	-	1.6	1.9	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>1)</sup>**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V},$ $f=1\text{ MHz}$	-	9100	11830	pF
Output capacitance	$C_{oss}$		-	1462	1900	
Reverse transfer capacitance	$C_{rss}$		-	61	92	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=100\text{ A}, R_G=3.5\ \Omega$	-	21	-	ns
Rise time	$t_r$		-	11	-	
Turn-off delay time	$t_{d(off)}$		-	49	-	
Fall time	$t_f$		-	38	-	

**Gate Charge Characteristics<sup>1)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=50\text{ V}, I_D=100\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	41	54	nC
Gate to drain charge	$Q_{gd}$		-	28	42	
Gate charge total	$Q_g$		-	128	166	
Gate plateau voltage	$V_{plateau}$		-	4.8	-	V

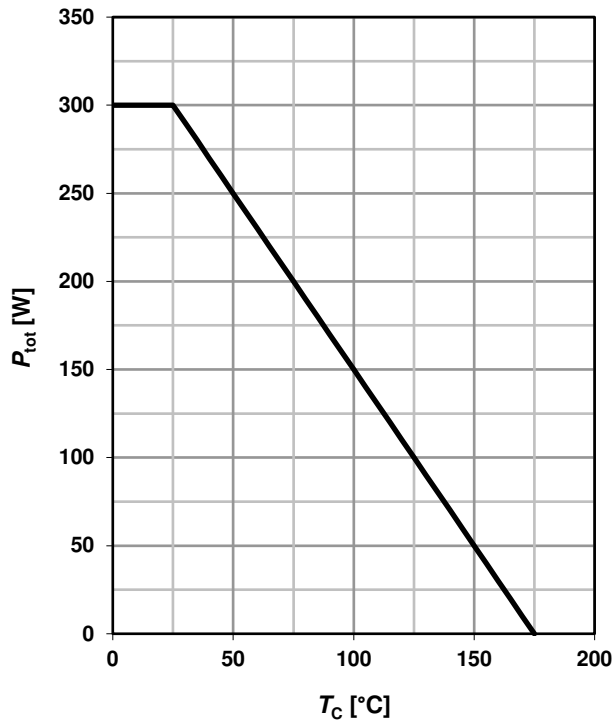
**Reverse Diode**

Diode continuous forward current <sup>1)</sup>	$I_S$	$T_C=25\text{ °C}$	-	-	260	A
Diode pulse current <sup>1)</sup>	$I_{S,pulse}$		-	-	1040	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=100\text{ A},$ $T_j=25\text{ °C}$	-	0.9	1.3	V
Reverse recovery time <sup>1)</sup>	$t_{rr}$	$V_R=50\text{ V}, I_F=50\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	80	-	ns
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$		-	180	-	nC

<sup>1)</sup> Defined by design. Not subject to production test.

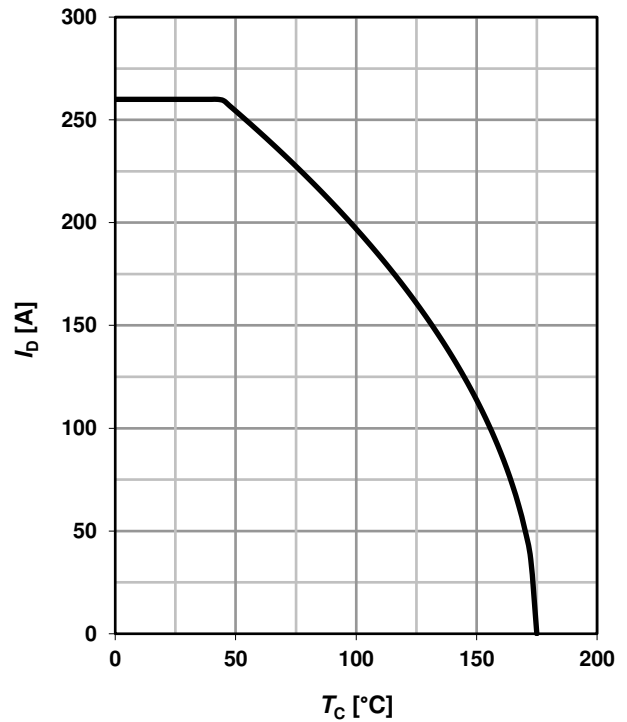
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



### 2 Drain current

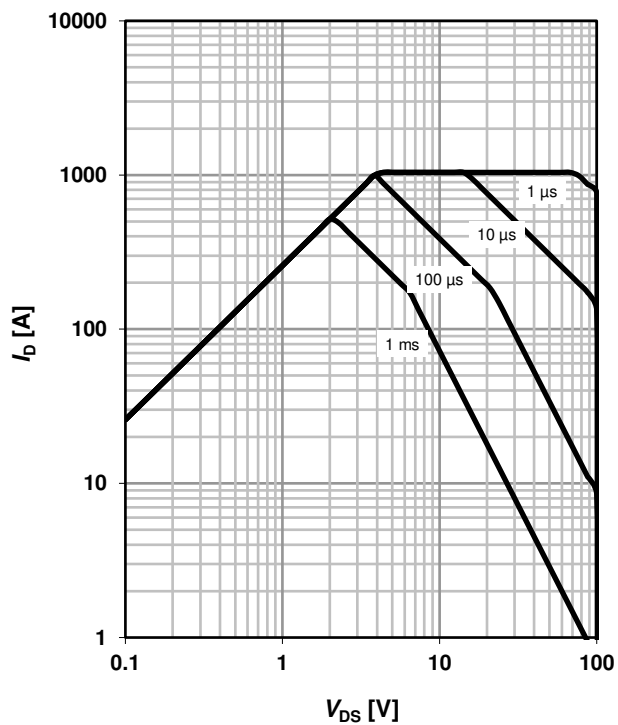
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

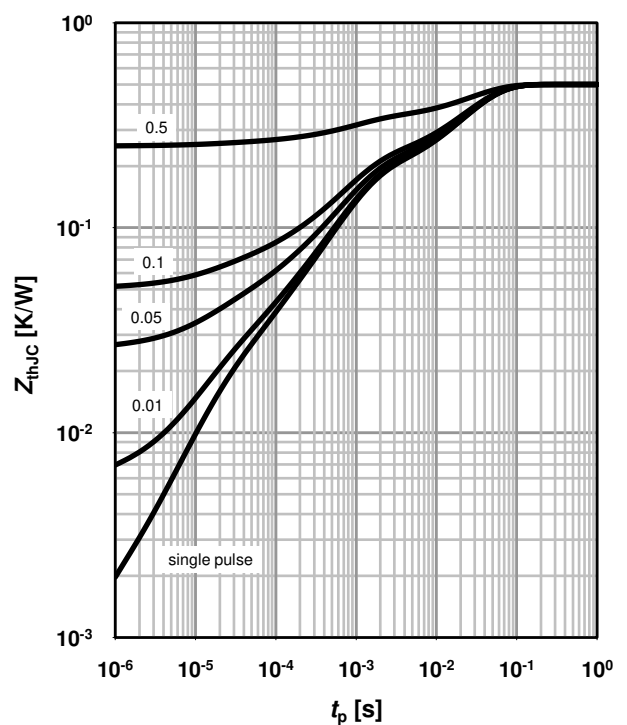
parameter:  $t_p$



### 4 Max. transient thermal impedance

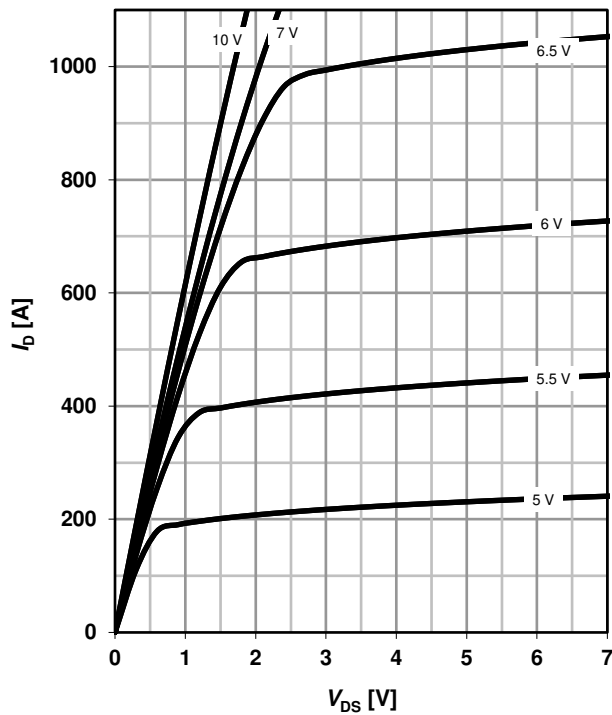
$$Z_{\text{thJC}} = f(t_p)$$

parameter:  $D = t_p/T$



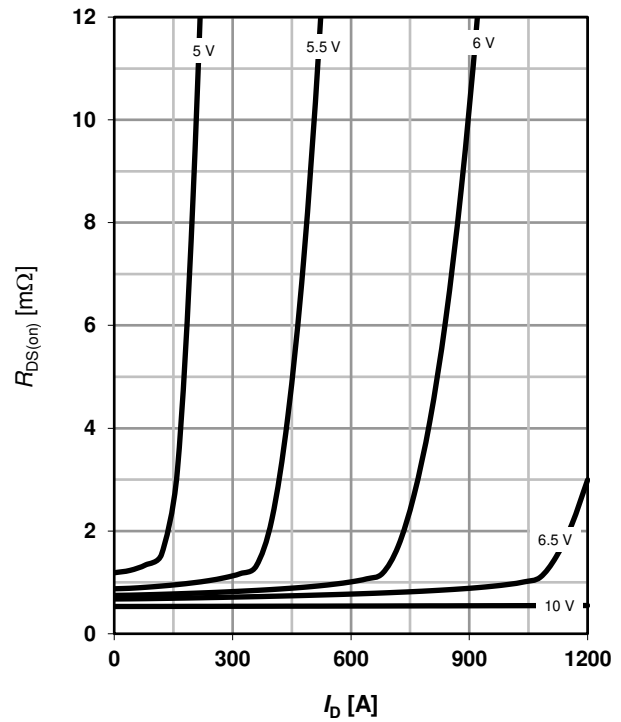
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25\text{ °C}$ 

 parameter:  $V_{GS}$ 


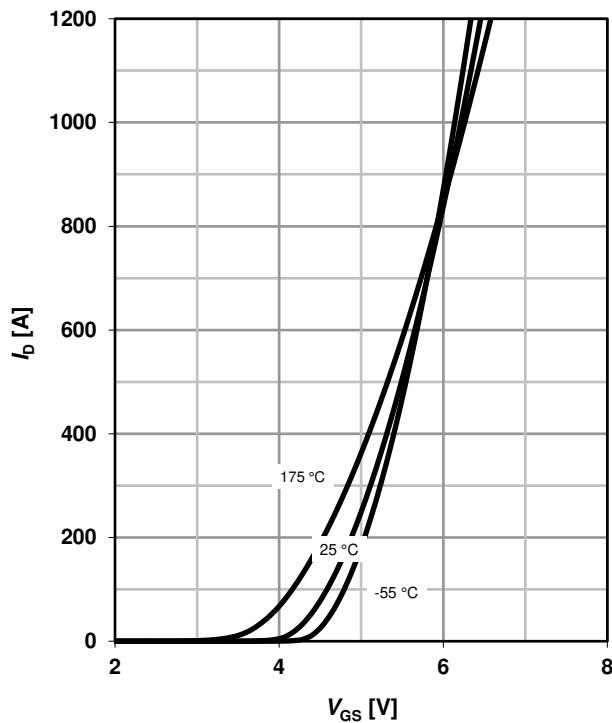
### 6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$ 

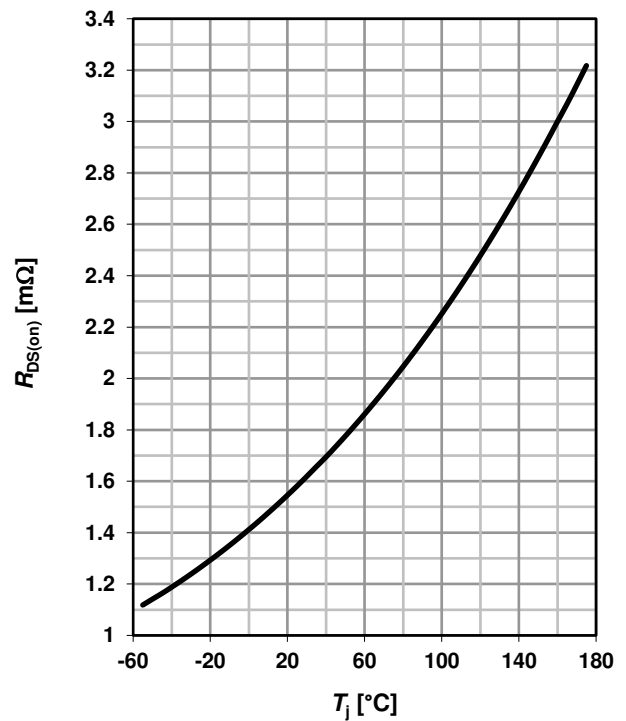
 parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{ V}$ 

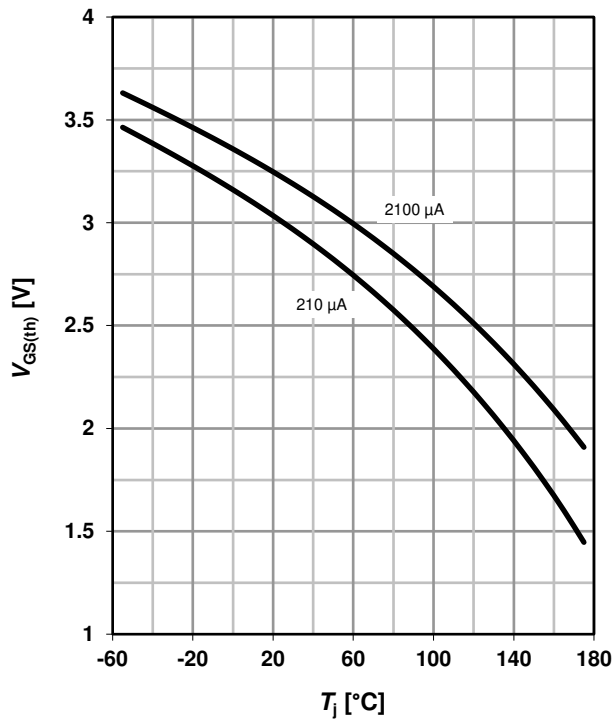
 parameter:  $T_j$ 


### 8 Typ. drain-source on-state resistance

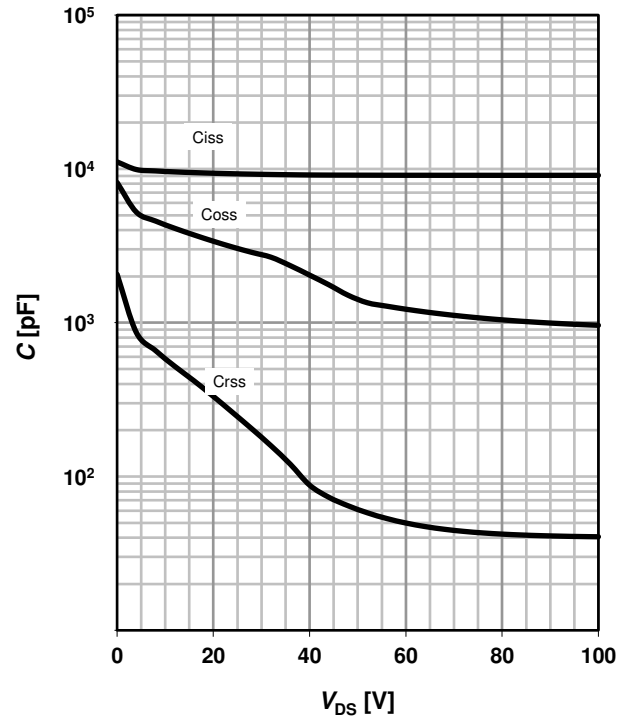
 $R_{DS(on)} = f(T_j); I_D = 100\text{ A}; V_{GS} = 10\text{ V}$ 


**9 Typ. gate threshold voltage**

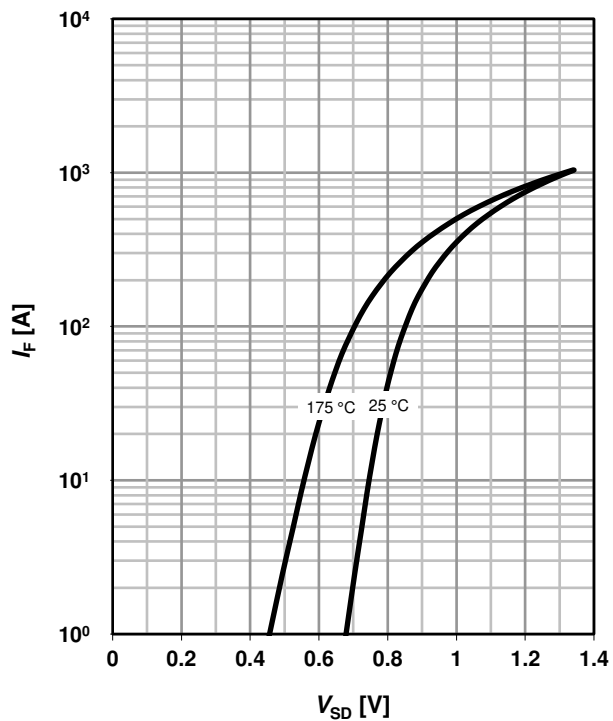
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

 parameter:  $I_D$ 

**10 Typ. capacitances**

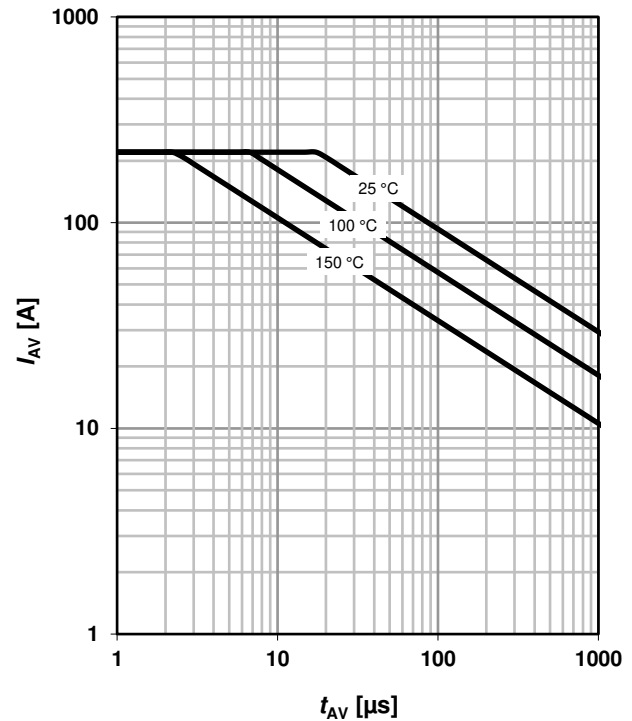
$$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$$


**11 Typical forward diode characteristics**

$$I_F = f(V_{SD})$$

 parameter:  $T_j$ 

**12 Typ. avalanche characteristics**

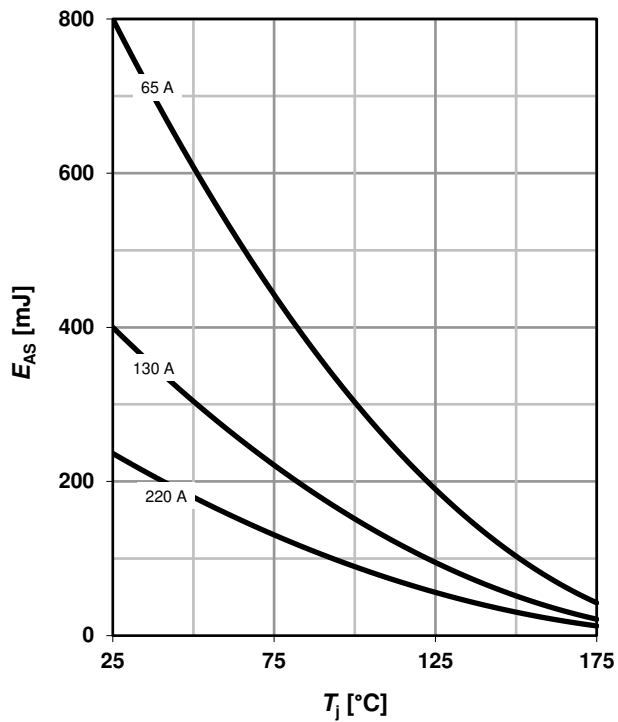
$$I_{AS} = f(t_{AV})$$

 parameter:  $T_{j(start)}$ 


### 13 Typical avalanche energy

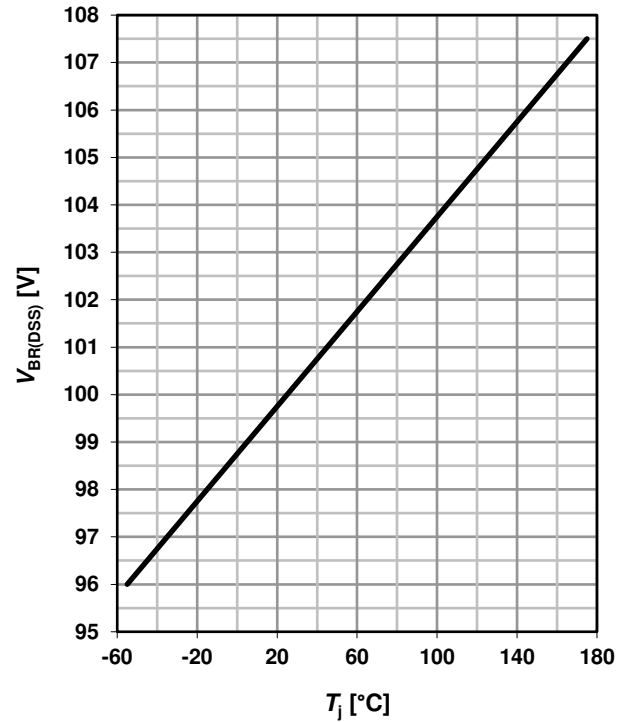
$$E_{AS} = f(T_j)$$

parameter:  $I_D$



### 14 Drain-source breakdown voltage

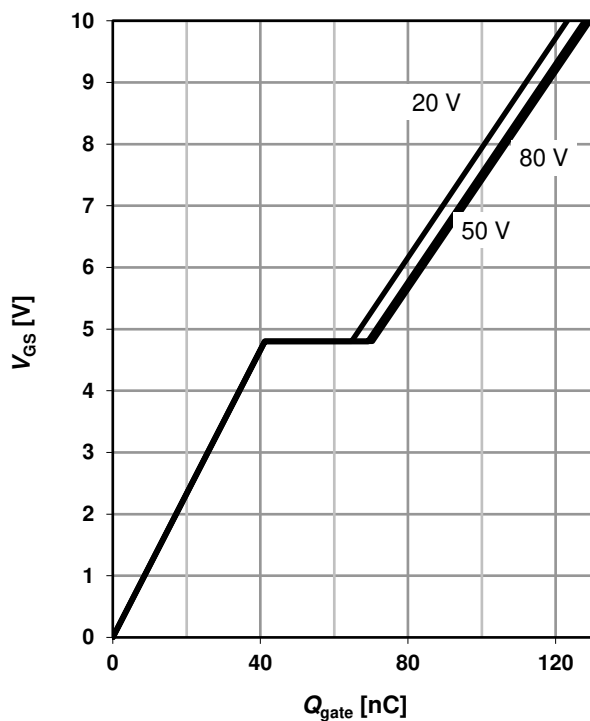
$$V_{BR(DSS)} = f(T_j); I_{D\_typ} = 1 \text{ mA}$$



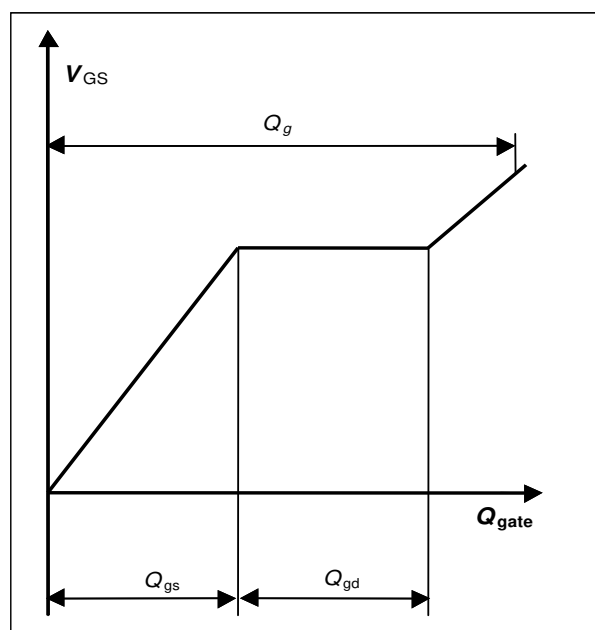
### 15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 100 \text{ A pulsed}$$

parameter:  $V_{DD}$



### 16 Gate charge waveforms



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## Revision History

Version	Date	Changes
Version 1.0	02.10.2017	Final Data Sheet
Version 2.0	14.03.2019	Updated avalanche parameters & $R_{DS(on)}$ 6V $I_D$ conditions